

	Type	L #	Hits	Search Text	DBs	Comments
1	BRS	L1	34542 2	438/\$.cccls. 257/\$.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
2	BRS	L2	1706	1 and (magnetic or permeable or NiFe or Ni-Fe or nikel-cobalt) near (shield or foil or layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
3	BRS	L3	137	2 and die	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
4	BRS	L4	13	3 and (encapsulant or (molded near (body or housing)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
5	BRS	L5	216	(tuttle-mark-e or deak-james-g).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
6	BRS	L6	66	5 and die	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
7	BRS	L8	1	7 and (magnetic or permeable or NiFe or Ni-Fe or nikel-cobalt) near (shield or foil or layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
8	BRS	L7	8	6 and (encapsulant or (molded near (body or housing)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
9	BRS	L9	31681	((magnetic or permeable or NiFe or Ni-Fe or nikel-cobalt) near (shield or foil or layer or film)).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
10	BRS	L11	13	2 and semiconductor near die	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
11	BRS	L12	3	11 and (encapsulant or (molded near (body or housing)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
12	BRS	L13	10789	semiconductor near die	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
13	BRS	L14	1639	13 and (encapsulant or (molded near (body or housing)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
14	BRS	L15	4	14 and (magnetic or permeable or NiFe or Ni-Fe or nikel-cobalt) near (shield or foil or layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
15	BRS	L17	133	2 and semiconductor near (die or chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	